

N-channel 40 V, 2.4 mΩ logic level MOSFET in LFPAK56

14 January 2025

Product data sheet

1. General description

Automotive gualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - Increases maximum current capability and improved current spreading •

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	163	W
Static chara	cteristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10		1.35	1.93	2.4	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic char	acteristics					·	
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13		-	5.9	11.7	nC
Source-drain	diode				·		
Qr	recovered charge	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	[2]	-	24.9	-	nC
S	softness factor	V _{DS} = 20 V		-	0.85	-	

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

[2] includes capacitive recovery

5. Pinning information

Table 2.	Pinning info	rmation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source	a	
4	G	gate		G_(F]▲)
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y2R4-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	<u>SOT669</u>		

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y2R4-40H	92H440

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage		[1]	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	163	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[2]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 2		-	600	А

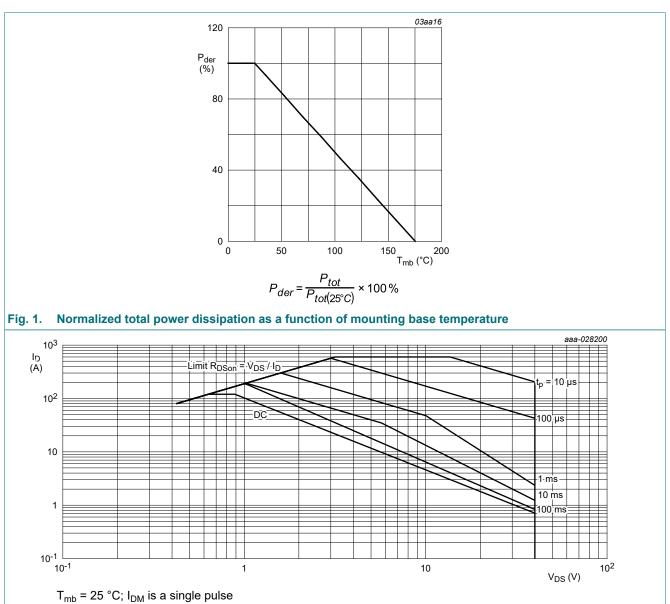
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					-
I _S	source current	T _{mb} = 25 °C		-	120	А
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	600	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_{D} = 120 \; A; \; V_{sup} \leq \; 40 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ \hline Fig. 3 \end{array} $	[3] [4]	-	81.5	mJ

[1] Refer to application note AN90001 for further information.

[2] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

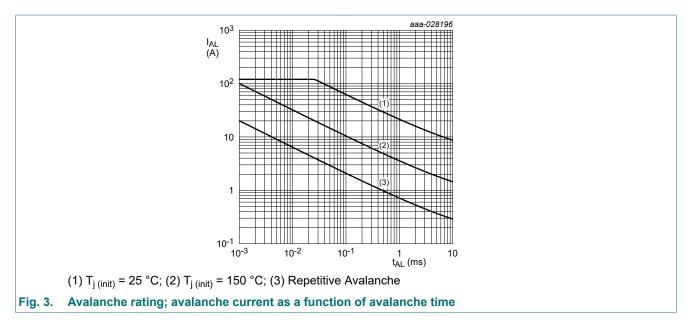
[4] Refer to application note AN10273 for further information.





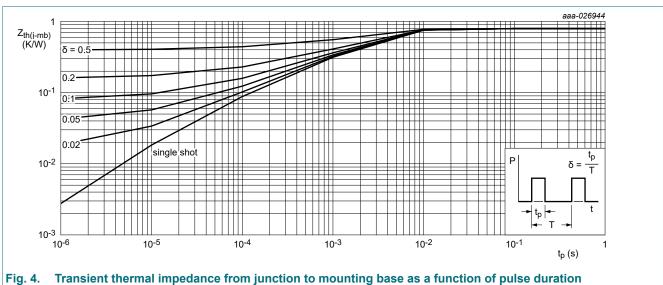
BUK9Y2R4-40H

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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.63	0.79	K/W



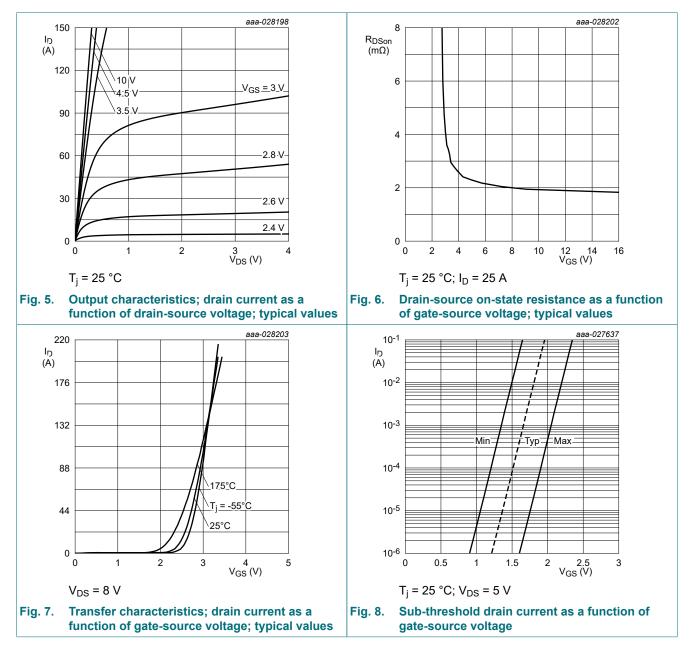
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	40	43	-	V
()	breakdown voltage	$I_D = 250 \ \mu\text{A}; V_{GS} = 0 \ \text{V}; T_i = -40 \ \text{°C}$	-	40.5	-	V
		$I_D = 250 \ \mu\text{A}; V_{GS} = 0 \ \text{V}; T_i = -55 \ \text{°C}$	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 8;</u> Fig. 9	1.35	1.66	2.05	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.6	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _i = -55 °C; <u>Fig. 9</u>	-	-	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _i = 25 °C	-	0.06	5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _i = 125 °C	-	1.2	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _i = 175 °C	-	142	500	μA
GSS	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.35	1.93	2.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 11	2	2.95	3.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.2	3.2	4.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	2.8	4.11	5.2	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.68	2.4	3.2	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 105 °C; <u>Fig. 11</u>	2.5	3.67	5	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.8	4	5.7	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; <u>Fig. 11</u>	3.5	5.11	7	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.29	0.72	1.8	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	55.8	78.2	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	25.3	35.4	nC
Q _{GS}	gate-source charge	Fig. 12; Fig. 13	-	9.9	14.9	nC
Q _{GD}	gate-drain charge		-	5.9	11.7	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	3960	5544	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	859	1203	pF
C _{rss}	reverse transfer capacitance		-	140	308	pF
d(on)	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	23.1	-	ns
r	rise time	$R_{G(ext)} = 5 \Omega$	-	26.3	-	ns
t _{d(off)}	turn-off delay time	1	-	27.2	-	ns
t _f	fall time	1	-	16.4	-	ns

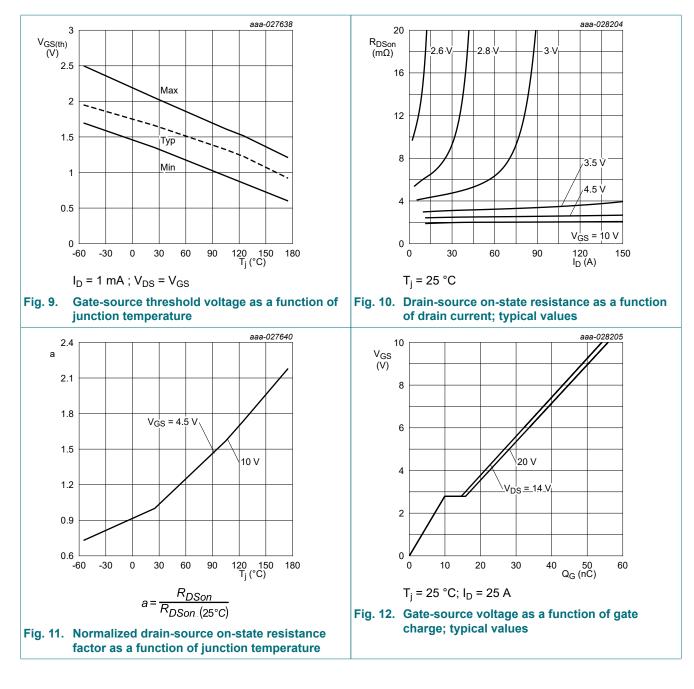
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Source-dra	in diode						
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	31	-	ns
Q _r	recovered charge	V _{DS} = 20 V	[1]	-	24.9	-	nC
S	softness factor	-		-	0.85	-	
		$ I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V} $		-	0.67	-	

[1] includes capacitive recovery

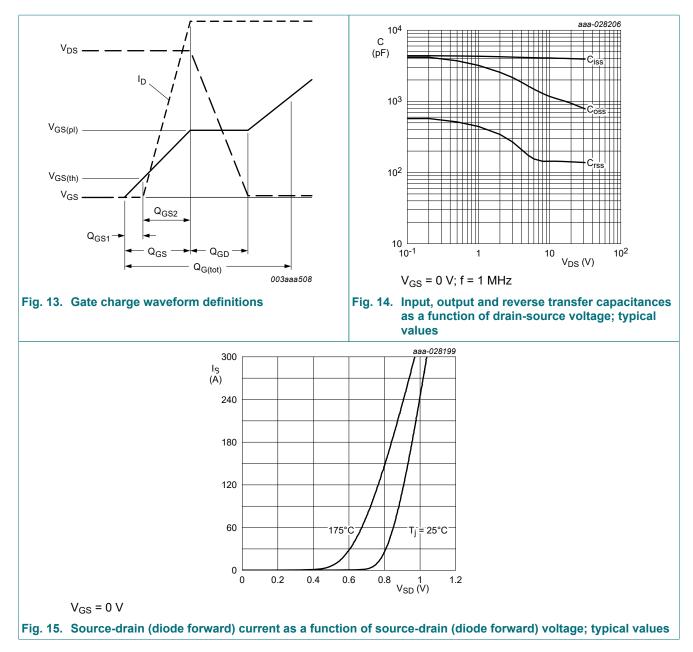


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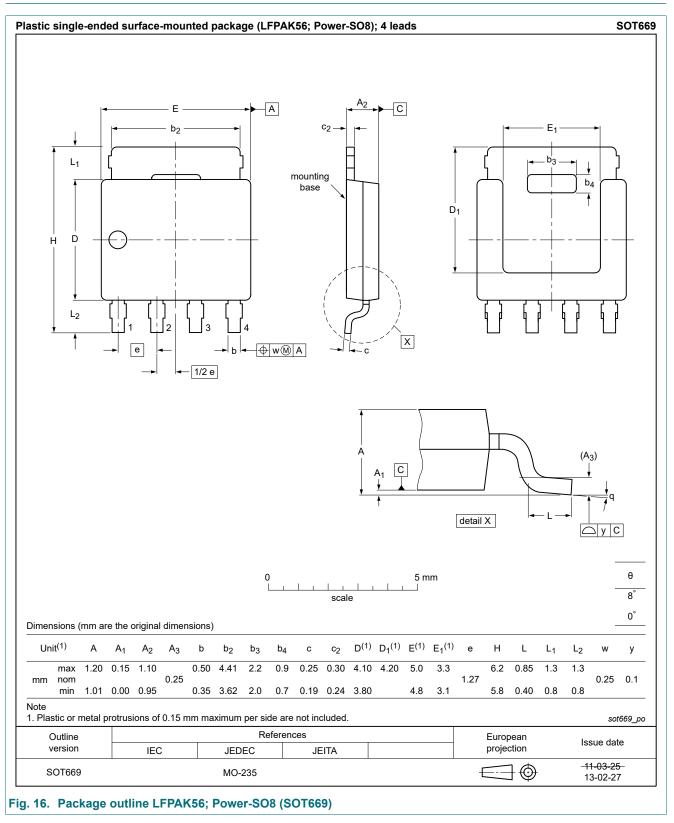


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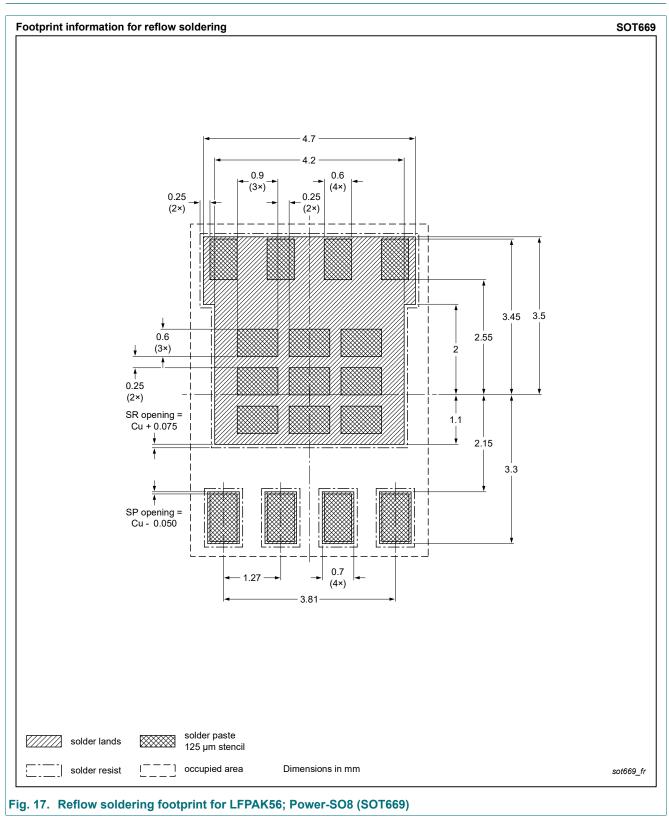
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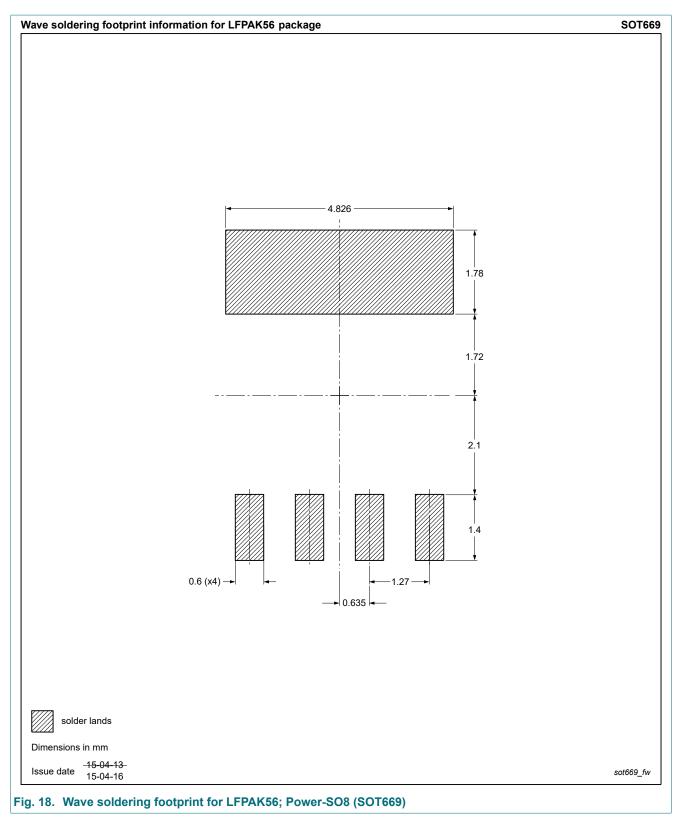
11. Package outline



12. Soldering



N-channel 40 V, 2.4 mΩ logic level MOSFET in LFPAK56



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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